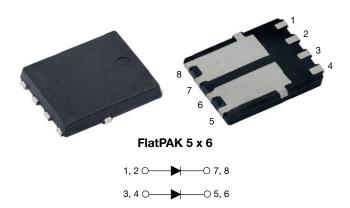
Vishay Semiconductors

Hyper Fast Rectifier, 2 x 4 A FRED Pt®



PRODUCT SUMMARY						
Package	FlatPAK 5 x 6					
I _{F(AV)}	2 x 4 A					
V _R	200 V					
V _F at I _F	0.7 V					
t _{rr (typ.)}	25 ns					
T _J max.	175 °C					
Diode variation	Separated cathode					

FEATURES

- Hyper fast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- Specific for output and snubber operation
- Low forward voltage drop
- Low leakage current
- AEC-Q101 qualified
- Meets MSL level 1 per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyper fast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyper fast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: FlatPAK 5 x 6

Molding compound meets UL 94 V-0 flamming rating Base P/NHM3 - halogen-free, RoHS-compliant, and AEC-Q101 qualified

Terminals: matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

HM3 suffix meets JESD 201 class 2 whisker test

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage		V _{RRM}		200	V		
Average restified forward surrent	per device	I	T _{Solderpad} = 170 °C, DC	8			
Average rectified forward current	per device	I _{F(AV)}	T _{Solderpad} = 169 °C, D = 0.5	0	А		
Non-repetitive peak surge current	per device		T _{.1} = 25 °C, 10 ms sinusoidal pulse	173			
Non-repetitive peak surge current	per diode	IFSM	$r_{\rm J} = 25$ °C, to this sinusoidal pulse	87			
Operating junction and storage temp	Operating junction and storage temperatures			-55 to +175	°C		

1

AUTOMOTIVE GRADE Available

> RoHS COMPLIANT HALOGEN FREE





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ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-		
	V _F	$I_F = 4 A$	-	0.87	0.96	V	
Forward voltage, per diode		I _F = 4 A, T _J = 150 °C	-	0.7	0.78		
Deverse leckers surrent ner diede	I _R	V _R = V _R rated	-	-	2		
Reverse leakage current, per diode		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	7	80	μA	
Junction capacitance	CT	V _R = 200 V	-	19	-	pF	

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	= 50 A/µs, V _R = 30 V	-	20	-		
Reverse recevent time	+	I _F = 0.5 A, I _R = 1 A	A, I _{rr} = 0.25 A	-	-	25	ns	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	17	-		
		T _J = 125 °C		-	29	-		
Deals recovery ourrent	1	T _J = 25 °C	$I_F = 4 A$	-	2.1	-	٨	
Peak recovery current	I _{RRM}	T _J = 125 °C	dl _F /dt = 200 A/µs V _R = 160 V	-	4	-	A	
Deverse we are started	0	T _J = 25 °C		-	18	-		
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	60	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C		
Thermal resistance, junction to ambient, per diode	R _{thJA} ⁽¹⁾⁽²⁾		-	89	103	°C/W		
Thermal resistance, junction to case, per diode	R _{thJC} ⁽³⁾		-	1.8	2.1	0/10		

Notes

 $^{(1)}$ The heat generated must be less than the thermal conductivity from junction to ambient: $dP_D/dT_J < 1/R_{thJA}$

 $^{(2)}$ Free air, mounted or recommended copper pad area; thermal resistance R_{thJA} - junction to ambient

⁽³⁾ Mounted on infinite heatsink



VS-8DKH02HM3

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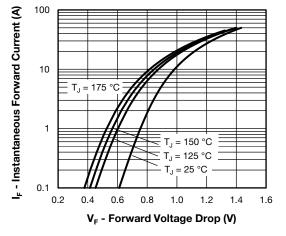


Fig. 1 - Typical Forward Voltage Drop Characteristics

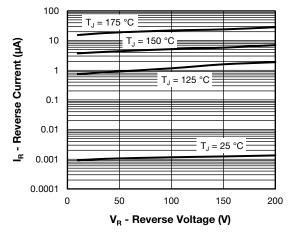


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

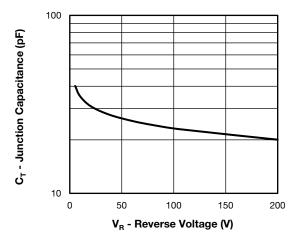


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

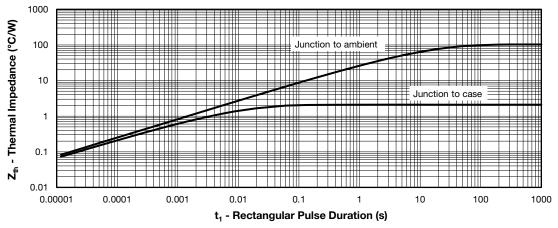


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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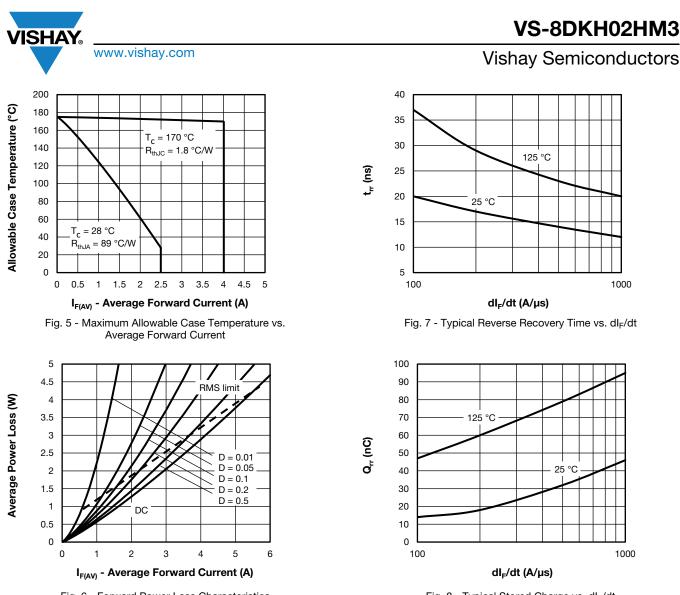


Fig. 6 - Forward Power Loss Characteristics



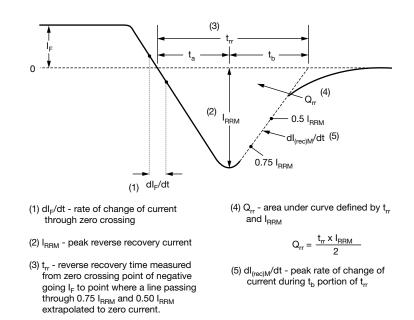


Fig. 9 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code	VS-	8	D	к	н	02	н	М3
	1	2	3	4	5	6	7	8
	2	- Cur	rent rati	niconduo ng (8 = 1	8 A)	oduct		
		D =	separat	iguratior ted cath	ode			
	H	- Pro	cess typ	K packa be, ast reco	-			
	E	- Volt	tage coo	le (02 = 101 qua	200 V)			
	8	- M3	= halog	en-free,	RoHS-0	complia	nt, and	termina

ORDERING INFORMATION (example)							
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	PACKAGING DESCRIPTION			
VS-8DKH02HM3/H	0.10	Н	1500	7"diameter plastic tape and reel			
VS-8DKH02HM3/I	0.10	I	6000	13"diameter plastic tape and reel			

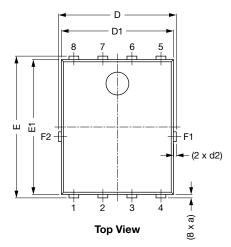
LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?96056					
Part marking information	www.vishay.com/doc?96059				
Packaging information	www.vishay.com/doc?88869				

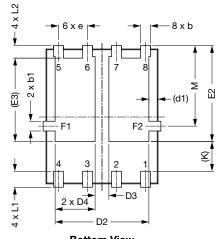




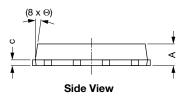
FlatPAK 5 x 6 (Dual)

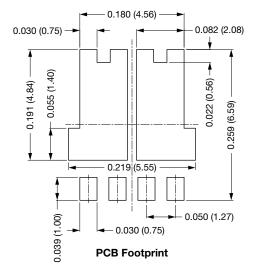
DIMENSIONS in inches (millimeters)











DIM		INCHES		MILLIMETERS		
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
А	0.035	0.039	0.043	0.89	0.99	1.09
(a)	-	0.006	-	-	0.15	-
b	0.013	0.017	0.020	0.32	0.43	0.52
b1	0.013	0.017	0.020	0.32	0.43	0.52
С	0.008	-	0.014	0.20	-	0.35
D	0.197	0.203	0.209	5.00	5.15	5.30
D1	0.189	0.193	0.197	4.80	4.90	5.00
D2	0.154	0.161	0.169	3.90	4.10	4.30
D3	0.020	0.024	0.031	0.50	0.60	0.80
D4	0.063	0.069	0.075	1.60	1.75	1.90
(d1)	-	0.016	-	-	0.40	-
(d2)	-	0.005	-	-	0.125	-
E	0.238	0.244	0.250	6.05	6.20	6.35

Revision: 27-Mar-18

1

Document Number: 96056

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Outline Dimensions



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DIM.		INCHES			MILLIMETERS		
DIN.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
E1	0.228	0.232	0.236	5.80	5.90	6.00	
E2	0.157	0.165	0.173	4.00	4.20	4.40	
(E3)	-	0.144	-	-	3.65	-	
е		0.050 BSC	1.27 BSC				
(K)	0.039	-	-	1.00	-	-	
L1	0.019	-	0.043	0.48	-	1.10	
L2	0.012	-	0.031	0.30	-	0.80	
М	0.128	0.138	0.148	3.25	3.50	3.75	
Θ	0°	-	10°	0°	-	10°	

Notes

٠ Dimensioning and tolerancing per ASME Y14.5-2009

Dimensions D1 and E1 do not include mold flash or gate burrs ٠

Dimension (XX) means reference only ٠



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